TOSHIBA

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP721F

OFFICE MACHINE SWITCHING POWER SUPPLY

The TOSHIBA TLP721F consists of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a four lead plastic DIP.

All parameters are tested to the specification of TLP721. (both condition and limits)

Collector-Emitter Voltage: 55V (Min.) Current Transfer Ratio : 50% (Min.) Rank GB : 100% (Min.)

	MADE IN	JAPAN	MADE IN T	THAILAND
UL Recognized	E67349	*1	E152349	*1
BSI Approved	7364, 7365	*2	7364, 7365	*2
SEMKO Approved	9325163	*3	9609169	*4
SEMICO Approved	9522142	*3		

- *1 UL1577
- *2 BS EN60065: 1994, BS EN60950: 1992
- *3 SS EN4330784
- *4 SS EN60950

10.16 ± 0.25 4.58 ± 0.25 7.62 ± 0.25 0.25MIN. 0.25 +0.1 10~12

TLP721F

Unit in mm

11-5B202

TOSHIBA 11-5B202 Weight: 0.28g

 2.54 ± 0.25

Option (D4) type VDE Approved

	MADE IN JAPAN	MADE IN THAILAND
VDE Approved	74285, 91835	91868
Maximum Operationg Insulation Voltage	890, 1130Vpk	1130Vpk
Highest Pernissible Over Voltage	6000, 8000Vpk	8000Vpk

*5 VDE0884/06.92

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

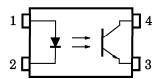
Creepage Distance 8.0mm (Min.) Clearance 8.0mm (Min.) Internal Creepage Path 4.0mm (Min.) Insulation Thickness 0.5mm (Min.)

Conforming Safety Standards:

DIN 57 804.VDE0804/1.83 DIN IEC65/VDE0860/8.81 DIN IEC380/VDE0806/8.81

DIN IEC435/VDE0805/Draft Nov.84 DIN IEC601T1/VDE0750T1/5.82 BS7002: 1989 (EN60950)

PIN CONFIGURATION (TOP VIEW)



- 1. ANODE
- 2. CATHODE
- 3. EMITTER
- 4. COLLECTOR

961001EBC2

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 Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.

 The products described in this document are subject to foreign exchange and foreign trade control laws.

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